

MOSFET, N-Channel, POWERTRENCH[®]

Q1: 30 V, 66 A, 4 mΩ

Q2: 30 V, 42 A, 5.5 mΩ

FDMD8900

General Description

This device utilizes two optimized N-ch FETs in a dual 3.3 x 5 mm thermally enhanced power package. The HS Source and LS drain are internally connected providing a low source inductance package, helping to provide the best FOM.

Features

Q1: N-Channel

- Max $r_{DS(on)}$ = 4 mΩ at $V_{GS} = 10$ V, $I_D = 19$ A
- Max $r_{DS(on)}$ = 5 mΩ at $V_{GS} = 4.5$ V, $I_D = 17$ A
- Max $r_{DS(on)}$ = 6.5 mΩ at $V_{GS} = 3.8$ V, $I_D = 15$ A
- Max $r_{DS(on)}$ = 8.3 mΩ at $V_{GS} = 3.5$ V, $I_D = 14$ A

Q2: N-Channel

- Max $r_{DS(on)}$ = 5.5 mΩ at $V_{GS} = 10$ V, $I_D = 17$ A
- Max $r_{DS(on)}$ = 6.5 mΩ at $V_{GS} = 4.5$ V, $I_D = 15$ A
- Max $r_{DS(on)}$ = 9 mΩ at $V_{GS} = 3.8$ V, $I_D = 13$ A
- Max $r_{DS(on)}$ = 12 mΩ at $V_{GS} = 3.5$ V, $I_D = 12$ A
- Ideal for Flexible Layout in Primary Side of Bridge Topology
- 100% UIL Tested
- Kelvin High Side MOSFET Drive Pin-out Capability
- This Device is Pb-Free and is RoHS Compliant

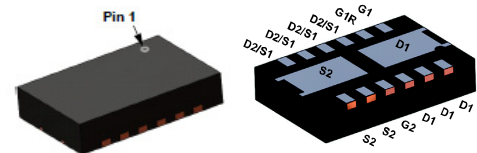
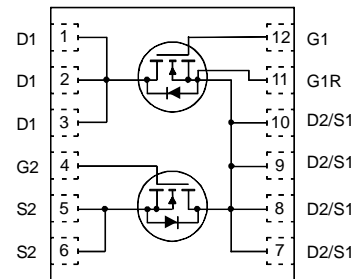
Applications

- Computing
- Buck, Boost and Buck/Boost Applications
- General Purpose POL



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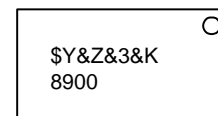
www.onsemi.com



Power 3.3 x 5

PQFN12 3.3X5, 0.65P
CASE 483BN

MARKING DIAGRAM



\$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
8900	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FDMD8900

MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, Unless otherwise noted)

Symbol	Parameter	Q1	Q2	Units
V _{DS}	Drain to Source Voltage	30	30	V
V _{GS}	Gate to Source Voltage	±12	±12	V
I _D	Drain Current –Continuous $T_C = 25^\circ\text{C}$ (Note 5)	66	42	A
	–Continuous $T_C = 100^\circ\text{C}$ (Note 5)	42	26	
	–Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	19	17	
	–Pulsed (Note 4)	280	210	
E _{AS}	Single Pulse Avalanche Energy (Note 3)	73	54	mJ
P _D	Power Dissipation $T_C = 25^\circ\text{C}$	27	15	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.1		
T _J , T _{STG}	Operating and Storage Junction Temperature Range	–55 to +150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Ratings	Unit
R _{θJC}	Thermal Resistance, Junction to Case	4.7	8.4	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient (Note 1a)	60		

PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Package	Shipping [†]
8900	FDMD8900	PQFN12 3.3x5, 0.65P (Pb-Free)	3000 units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

FDMD8900

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Type	Min.	Typ.	Max.	Units
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OFF CHARACTERISTICS

BV _{DSS}	Drain to Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V I _D = 250 μA, V _{GS} = 0 V	Q1 Q2	30 30			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25°C I _D = 250 μA, referenced to 25°C	Q1 Q2	14 13			mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V V _{DS} = 24 V, V _{GS} = 0 V	Q1 Q2			1 1	μA
I _{GSS}	Gate to Source Leakage Current	V _{GS} = ±12 V, V _{DS} = 0 V V _{GS} = ±12 V, V _{DS} = 0 V	Q1 Q2			±100 ±100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate to Source Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA V _{GS} = V _{DS} , I _D = 250 μA	Q1 Q2	0.8 1	1.3 1.4	2.5 2.5	V
ΔV _{GS(th)} ΔT _J	Gate to Source Threshold Voltage Temperature Coefficient	I _D = 250 mA, referenced to 25°C I _D = 250 mA, referenced to 25°C	Q1 Q2		-4 -4		mV/°C
r _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10 V, I _D = 19 A V _{GS} = 4.5 V, I _D = 17 A V _{GS} = 3.8 V, I _D = 15 A V _{GS} = 3.5 V, I _D = 14 A V _{GS} = 10 V, I _D = 19 A, T _J = 125°C	Q1		3.4 4 4.3 4.6 4.6	4 5 6.5 8.3 6	mΩ
		V _{GS} = 10 V, I _D = 17 A V _{GS} = 4.5 V, I _D = 15 A V _{GS} = 3.8 V, I _D = 13 A V _{GS} = 3.5 V, I _D = 12 A V _{GS} = 10 V, I _D = 17 A, T _J = 125°C	Q2		4.5 5.4 6 6.6 5.8	5.5 6.5 9 12 6.9	
g _{FS}	Forward Transconductance	V _{DS} = 5 V, I _D = 19 A V _{DS} = 5 V, I _D = 17 A	Q1 Q2		86 80		S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	Q1: V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Q1 Q2	1735 1210	2605 1815	pF
C _{oss}	Output Capacitance	Q2: V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Q1 Q2	462 356	695 535	pF
C _{rss}	Reverse Transfer Capacitance		Q1 Q2	47 52	75 80	pF
R _g	Gate Resistance		Q1 Q2	0.8 1.9		W

SWITCHING CHARACTERISTICS

t _{d(on)}	Turn-On Delay Time	Q1: V _{DD} = 15 V, I _D = 19 A, R _{GEN} = 6 Ω	Q1 Q2	8.7 7.1	17 14	ns	
t _r	Rise Time	Q2: V _{DD} = 15 V, I _D = 17 A, R _{GEN} = 6 Ω	Q1 Q2	2.3 2	10 10	ns	
t _{d(off)}	Turn-Off Delay Time		Q1 Q2	25 22	40 35	ns	
t _f	Fall Time		Q1 Q2	2.4 2.3	10 10	ns	
Q _g	Total Gate Charge	V _{GS} = 0 V to 10 V	Q1: V _{DD} = 15 V, I _D = 19 A Q2: V _{DD} = 15 V, I _D = 17 A	Q1 Q2	25 19	35 27	nC
Q _g	Total Gate Charge	V _{GS} = 0 V to 4.5 V		Q1 Q2	12 8.8	17 12	nC
Q _{gs}	Gate to Source Gate Charge		Q1 Q2	3.6 2.7		nC	
Q _{gd}	Gate to Drain "Miller" Charge		Q1 Q2	2.7 2.6		nC	

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Type	Min.	Typ.	Max.	Units
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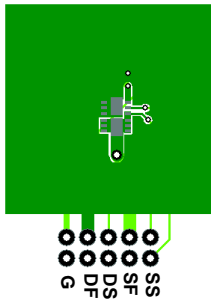
DRAIN-SOURCE DIODE CHARACTERISTICS $T_J = 25^\circ\text{C}$ unless otherwise noted.

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 19\text{ A}$ (Note 2) $V_{GS} = 0\text{ V}, I_S = 17\text{ A}$ (Note 2)	Q1 Q2		0.8 0.8	1.2 1.2	V
t_{rr}	Reverse Recovery Time	Q1: $I_F = 19\text{ A}, \Delta i/\Delta t = 100\text{ A/ms}$	Q1 Q2		26 22	42 35	ns
Q_{rr}	Reverse Recovery Charge	Q2: $I_F = 17\text{ A}, \Delta i/\Delta t = 100\text{ A/ms}$	Q1 Q2		10 7.8	20 16	nC

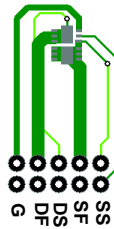
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

- $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 60 °C/W when mounted on a 1 in² pad of 2 oz copper



b. 130 °C/W when mounted on a minimum pad of 2 oz copper

- Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0 %.
- Q1: E_{AS} of 73 mJ is based on starting $T_J = 25^\circ\text{C}$, $L = 3\text{ mH}$, $I_{AS} = 7\text{ A}$, $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$. 100% tested at $L = 0.1\text{ mH}$, $I_{AS} = 25\text{ A}$.
Q2: E_{AS} of 54 mJ is based on starting $T_J = 25^\circ\text{C}$, $L = 3\text{ mH}$, $I_{AS} = 6\text{ A}$, $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$. 100% tested at $L = 0.1\text{ mH}$, $I_{AS} = 20\text{ A}$.
- Pulse Id refers to Figure "Forward Bias Safe Operation Area".
- Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

TYPICAL CHARACTERISTICS (Q1 N-CHANNEL) $T_J = 25^\circ\text{C}$ unless otherwise noted.

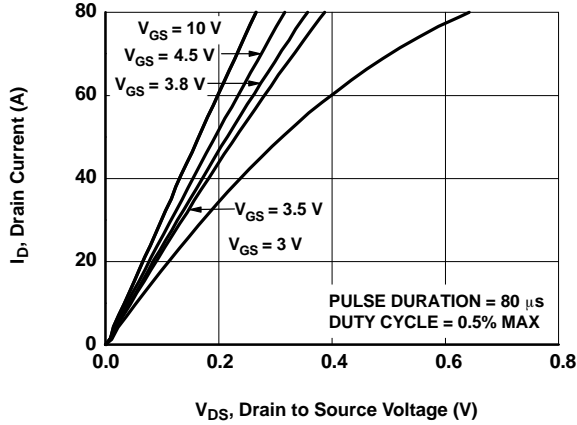


Figure 1. On-Region Characteristics

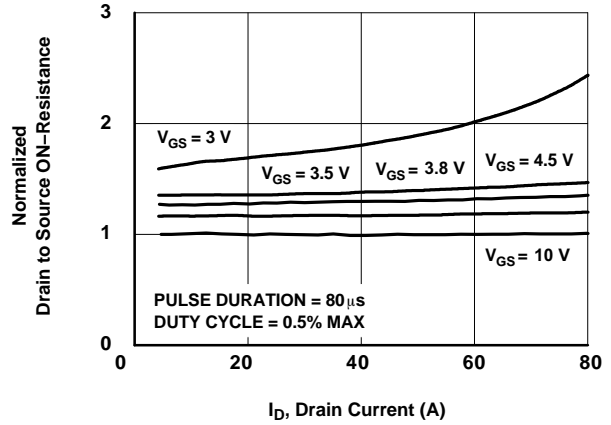


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

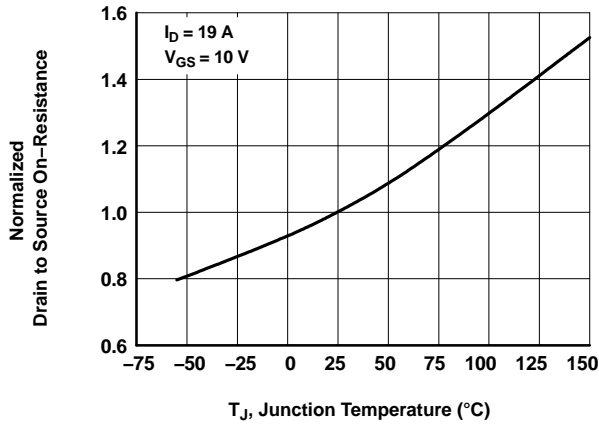


Figure 3. Normalized On Resistance vs. Junction Temperature

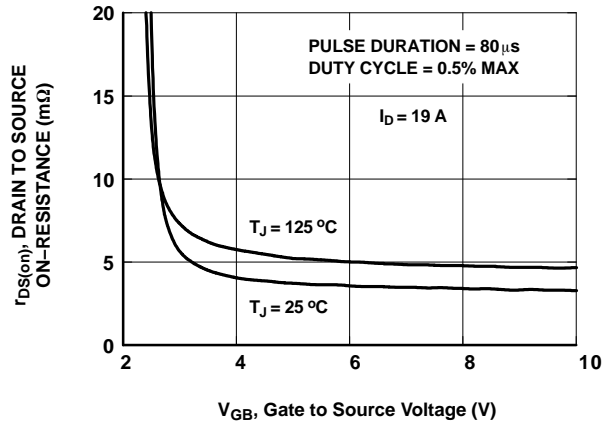


Figure 4. On Resistance vs. Gate to Source Voltage

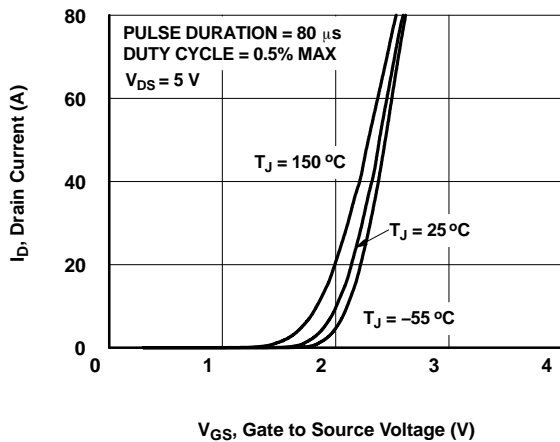


Figure 5. Transfer Characteristics

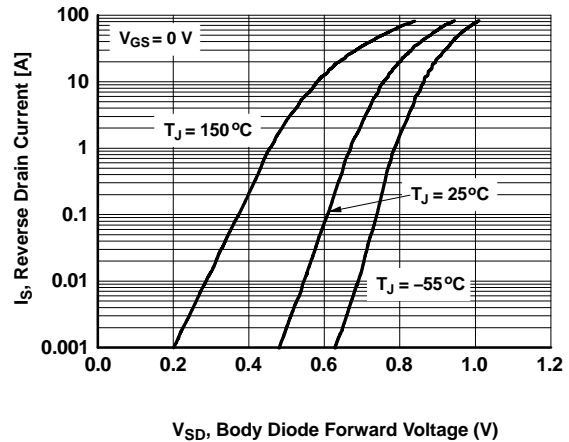


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

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TYPICAL CHARACTERISTICS (Q1 N-CHANNEL) $T_J = 25^\circ\text{C}$ unless otherwise noted.

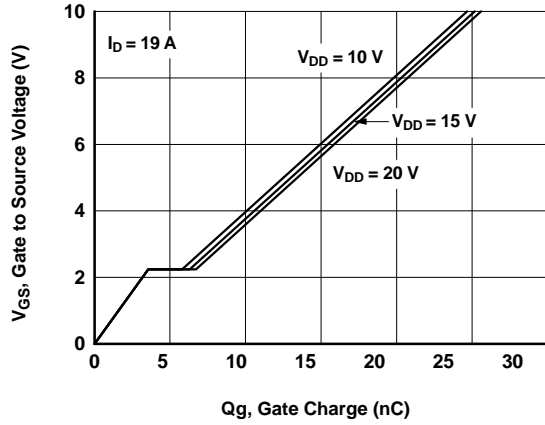


Figure 7. Gate Charge Characteristics

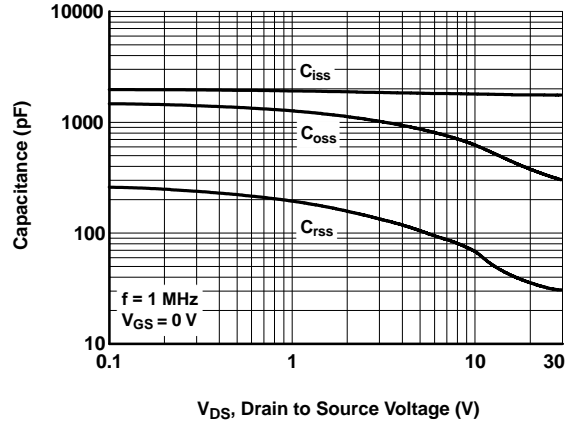


Figure 8. Capacitance vs. Drain to Source Voltage

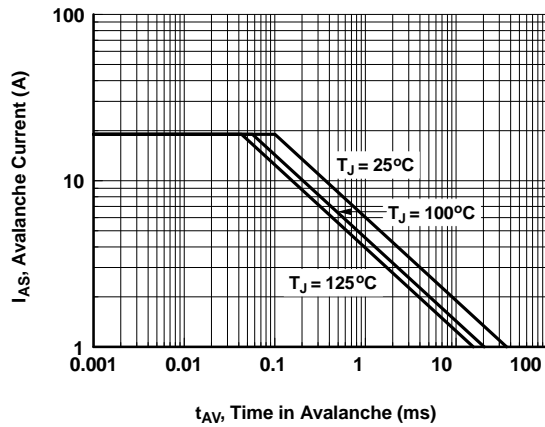


Figure 9. Unclamped Inductive Switching Capability

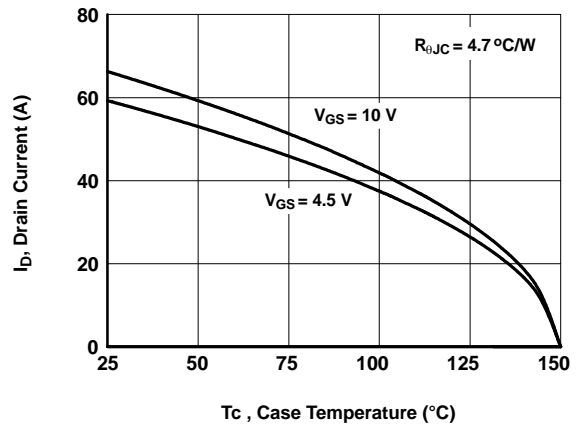


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

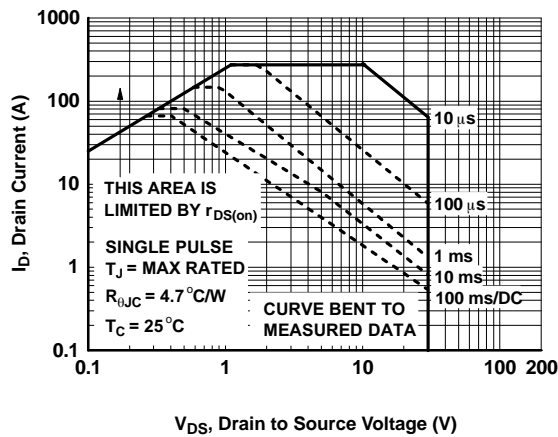


Figure 11. Forward Bias Safe Operating Area

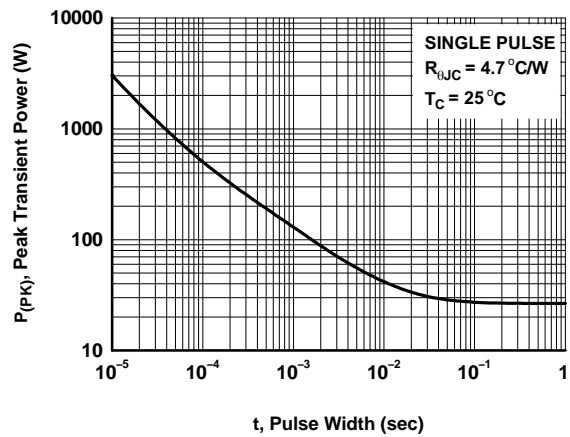


Figure 12. Single Pulse Maximum Power Dissipation

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TYPICAL CHARACTERISTICS (Q1 N-CHANNEL) $T_J = 25^\circ\text{C}$ unless otherwise noted.

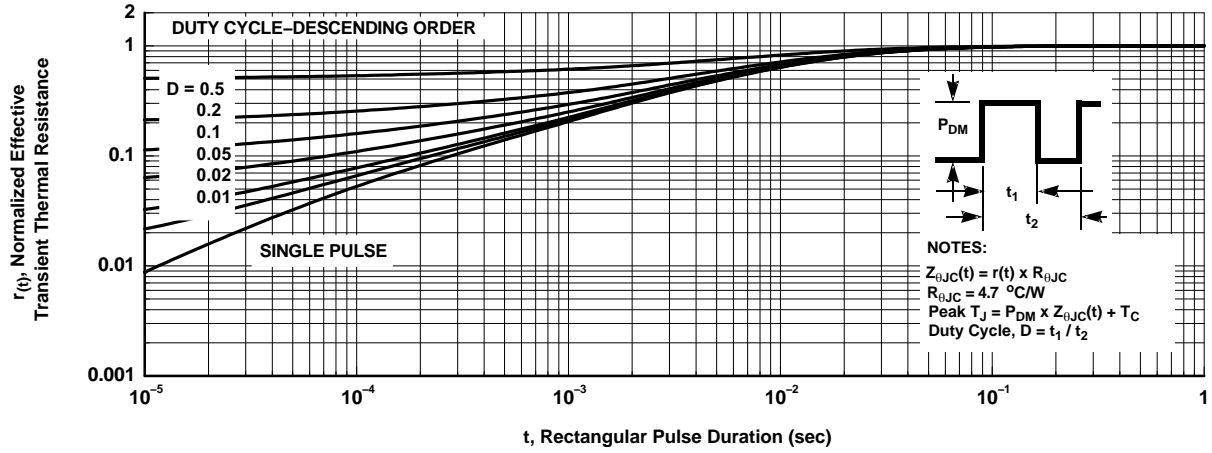


Figure 13. Junction-to-Case Transient Thermal Response Curve

TYPICAL CHARACTERISTICS (Q2 N-CHANNEL) $T_J = 25^\circ\text{C}$ unless otherwise noted.

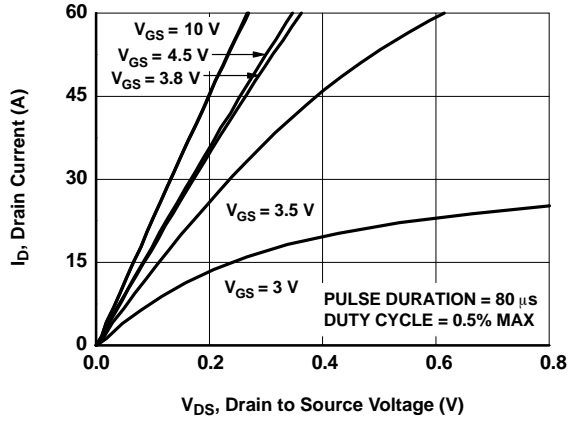


Figure 14. On-Region Characteristics

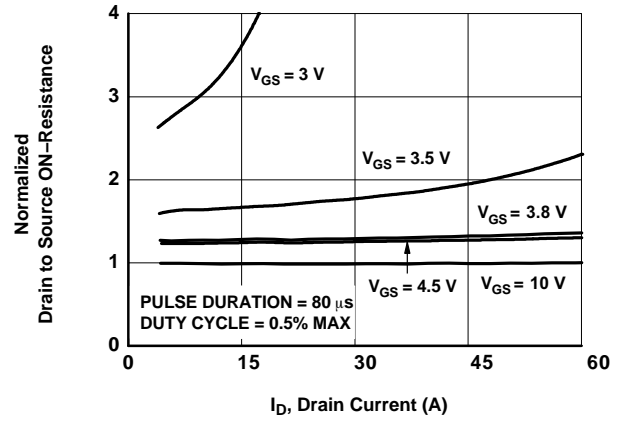


Figure 15. Normalized On-Resistance vs. Drain Current and Gate Voltage

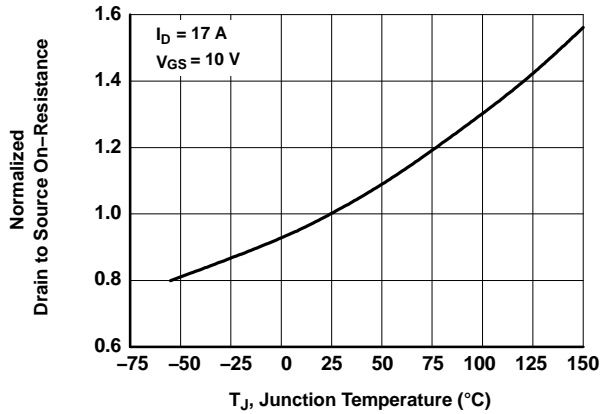


Figure 16. Normalized On-Resistance vs. Junction Temperature

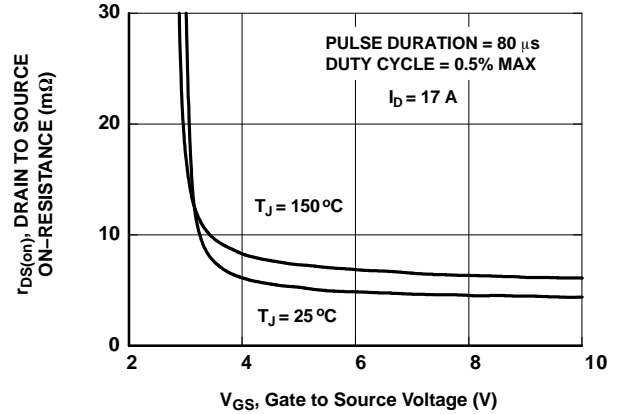


Figure 17. On Resistance vs. Gate to Source Voltage

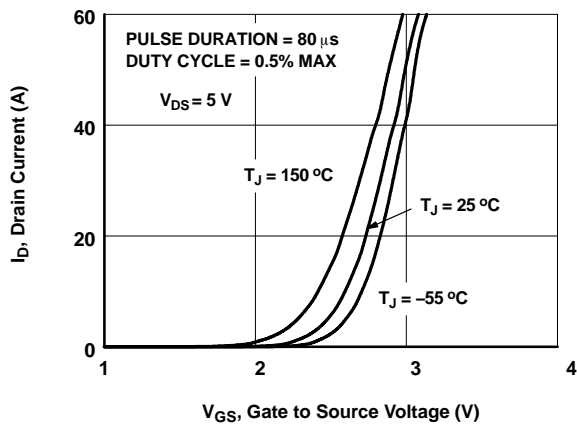


Figure 18. Transfer Characteristics

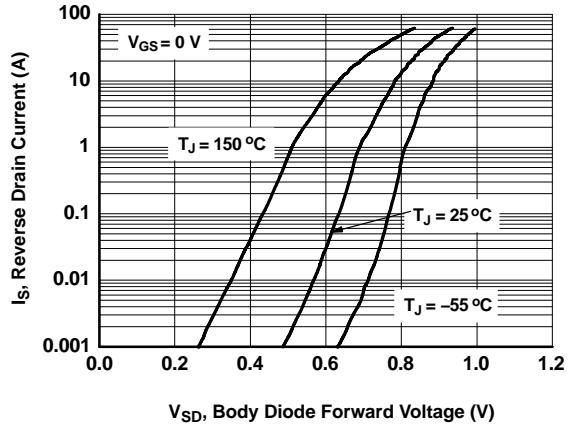


Figure 19. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (Q2 N-CHANNEL) $T_J = 25^\circ\text{C}$ unless otherwise noted.

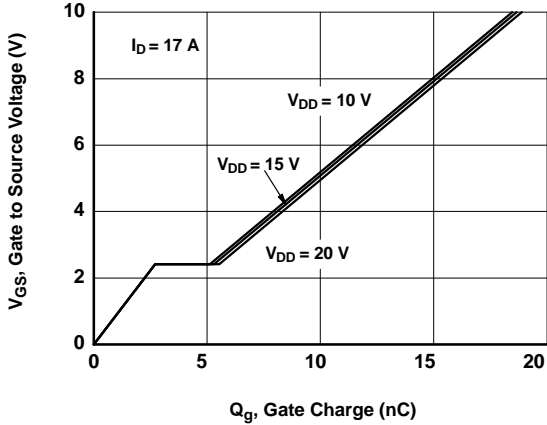


Figure 20. Gate Charge Characteristics

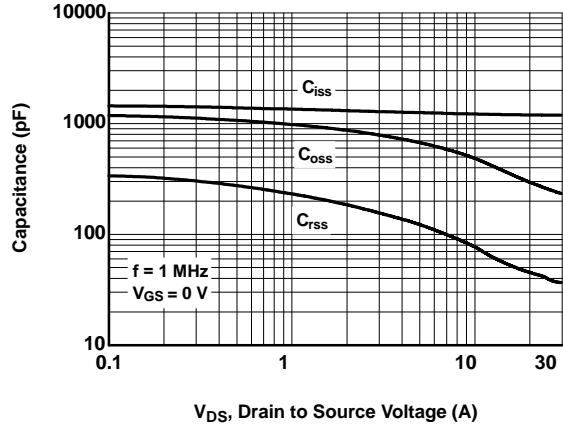


Figure 21. Capacitance vs. Drain to Source Voltage

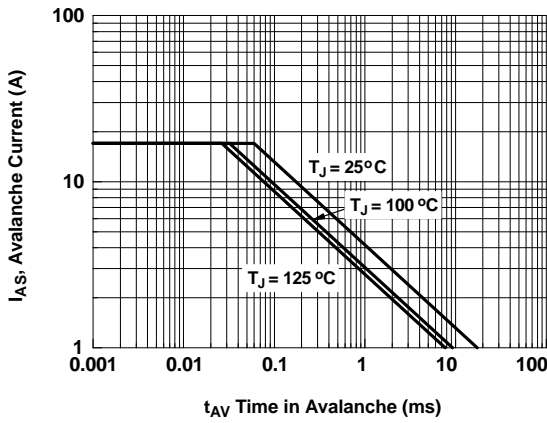


Figure 22. Unclamped Inductive Switching Capability

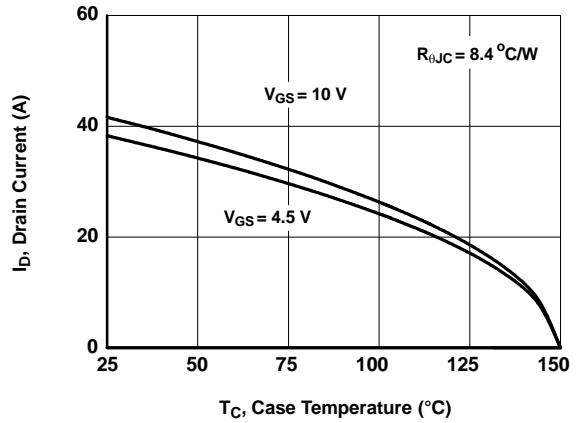


Figure 23. Maximum Continuous Drain Current vs. Case Temperature

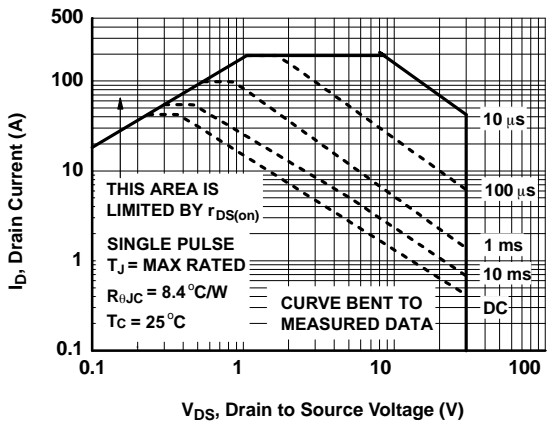


Figure 24. Forward Bias Safe Operating Area

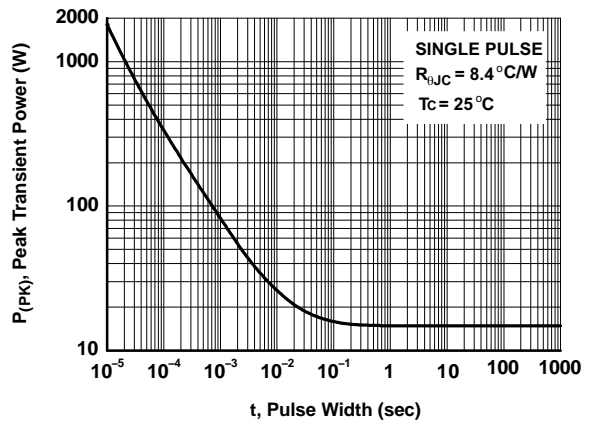


Figure 25. Single Pulse Maximum Power Dissipation

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TYPICAL CHARACTERISTICS (Q2 N-CHANNEL) $T_J = 25^\circ\text{C}$ unless otherwise noted.

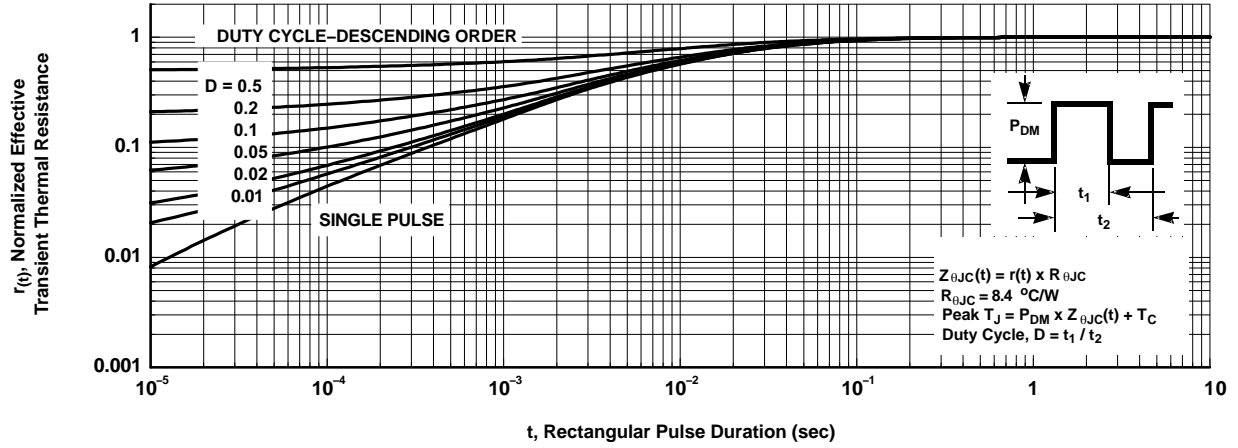


Figure 26. Junction-to-Case Transient Thermal Response Curve

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MECHANICAL CASE OUTLINE

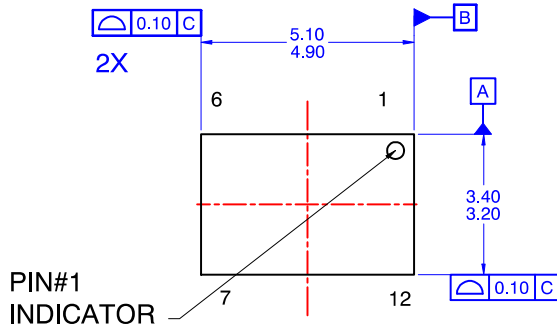
PACKAGE DIMENSIONS

ON Semiconductor®

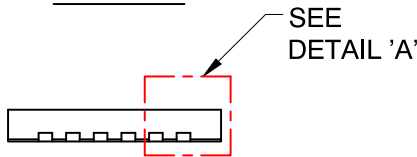


PQFN12 3.3X5, 0.65P
CASE 483BN
ISSUE O

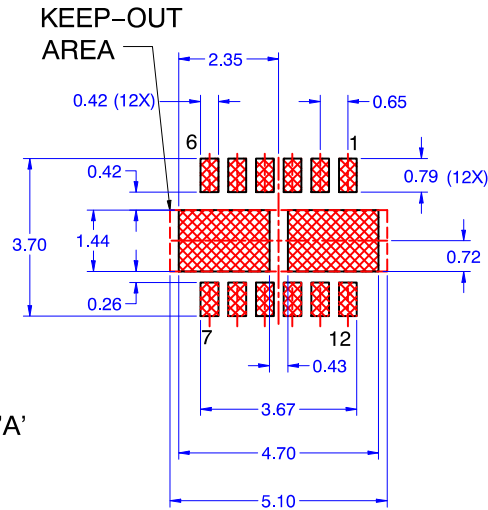
DATE 30 SEP 2016



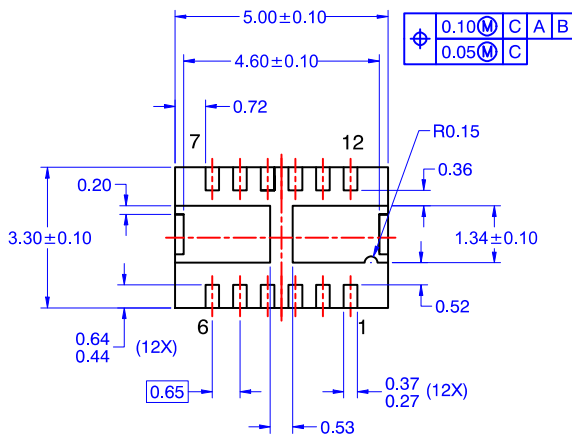
TOP VIEW



FRONT VIEW



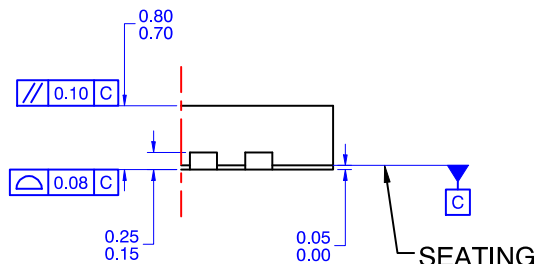
LAND PATTERN RECOMMENDATION



BOTTOM VIEW

NOTES: UNLESS OTHERWISE SPECIFIED

- A) DOES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229 DATED 8/2012
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- E) IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.



DETAIL 'A'

SCALE: 2:1

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STATUS:	ON SEMICONDUCTOR STANDARD	
NEW STANDARD:		
DESCRIPTION:	PQFN12 3.3X5, 0.65P	PAGE 1 OF 2



ISSUE	REVISION	DATE
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